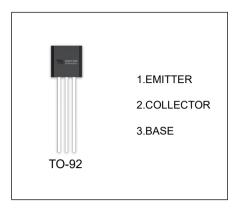


2N6727 TRANSISTOR (PNP)

FEATURES

General Purpose Switching Application



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N6727	TO-92	Bulk	1000pcs/Bag
2N6727-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RA TINGS (Ta =25 $^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-1.5	Α
Pc	Collector Power Dissipation	1	W
R _{θJA}	R _{θJA} Thermal Resistance From Junction To Ambient		°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I_C = -1mA, I_E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V,I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-40V,I _E =0			-1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-0.1	μΑ
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-1A	50		250	
	h _{FE(2)}	V _{CE} =-1V, I _C =-10mA	55			
	h _{FE(3)}	V _{CE} =-1V, I _C =-100mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A,I _B =-100mA			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-1A			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0, f=1MHz			30	pF



